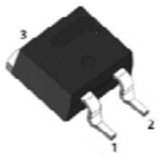
Silicon Carbide Schottky Diode

V_{RRM}	=	1200 V
I_F (T_C=151 ℃)	=	10 A
Q_C	=	61 nC

Features

- 1.2kV Schottky Rectifier
- Zero Reverse Recovery Current
- High-Frequency Operation
- Temperature-Independent Switching
- Extremely Fast Switching

Package



TO-263-2

RoHS

Benefits

- Replace Bipolar with Unipolar Rectifiers
- Essentially No Switching Losses
- High Efficiency
- Reduction of Heat Sink Requirements
- Parallel Devices Without Thermal Runaway

Applications

- Switching Mode Power Supply
- Boost Diodes in PFC
- DC/DC Converters
- AC/DC Converters
- Free Wheeling Diodes in Inverter

Maximum Ratings （Tc = 25 ℃ unless otherwise specified）

Symbol	Parameter	Value	Unit	Test Conditions	Note
V_{RRM}	Repetitive Peak Reverse Voltage	1200	V		
V_{RSM}	Surge Peak Reverse Voltage	1300	V		
V_R	DC Peak Reverse Voltage	1200	V		
I_F	Continuous Forward Current	30 14 10	A	T_C=25 ℃ T_C=135 ℃ T_C=151 ℃	Fig. 3
I_{FSM}	Non-Repetitive Forward Surge Current	80	A	T_C=25 ℃，t_p=10 ms，Half Sine Pulse	
P_{tot}	Power Dissipation	136 59	W	T_C=25 ℃ T_C=110 ℃	Fig. 4
T_J	Operating Junction Range	-55 to +175	℃		
T_{stg}	Storage Temperature Range	-55 to +175	℃		

Electrical Characteristics

Symbol	Parameter	Typ.	Max.	Unit	Test Conditions	Note
V_F	Forward Voltage	1.45 2.0	1.7 2.6	V	I_F = 10 A， T_J = 25 ℃ I_F = 10 A， T_J = 175 ℃	Fig. 1
I_R	Reverse Current	4 30	100 300	μA	V_R = 1200 V，T_J = 25 ℃ V_R = 1200 V，T_J = 175 ℃	Fig. 2
Q_C	Total Capacitive Charge	61		nC	V_R = 800 V，I_F = 10 A， T_J = 25 ℃	Fig. 6
C	Total Capacitance	800 57 42		pF	V_R = 0 V， T_J = 25 ℃，f = 1 MHz V_R = 400 V，T_J = 25 ℃，f = 1 MHz V_R = 800 V，T_J = 25 ℃，f = 1 MHz	Fig. 5
E_C	Capacitance Stored Energy	15.6		μJ	V_R = 800 V	Fig. 7

Note：This is a majority carrier diode, so there is no reverse recovery charge.

Thermal Characteristics

Symbol	Parameter	Min.	Typ.	Max.	Unit	Note
$R_{\theta JC}$	Thermal Resistance from Junction to Case		1.1		℃/W	Fig.8

Typical Performance

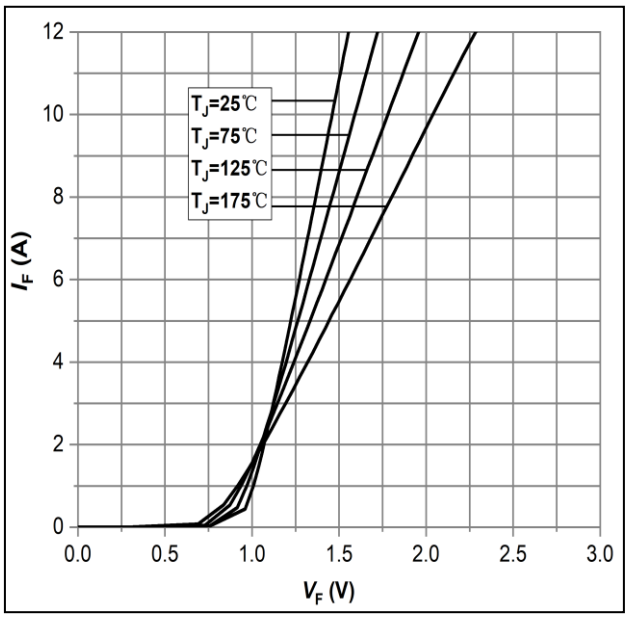


Figure 1: Forward Characteristics

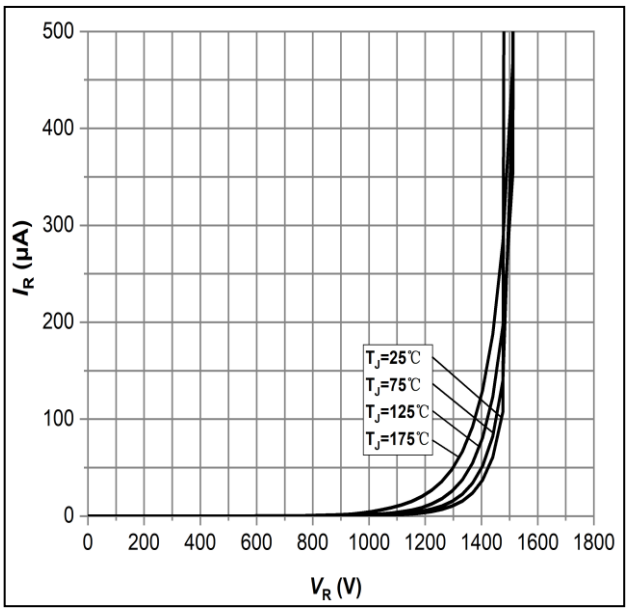


Figure 2: Reverse Characteristics

Typical Performance

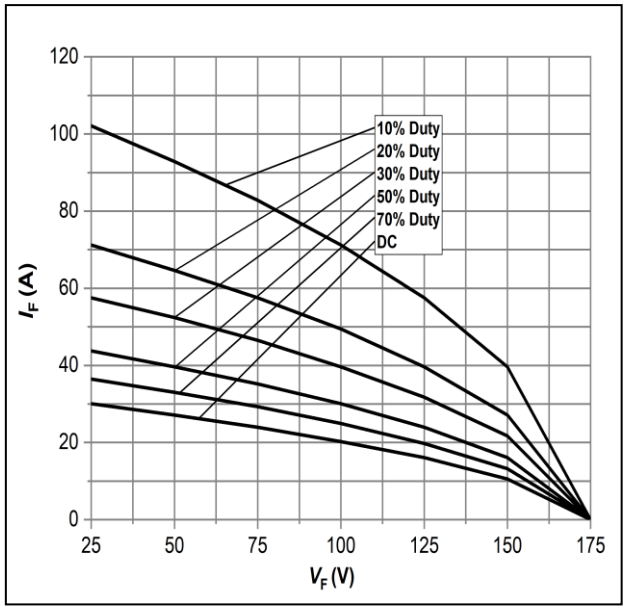


Figure 3: Current Derating

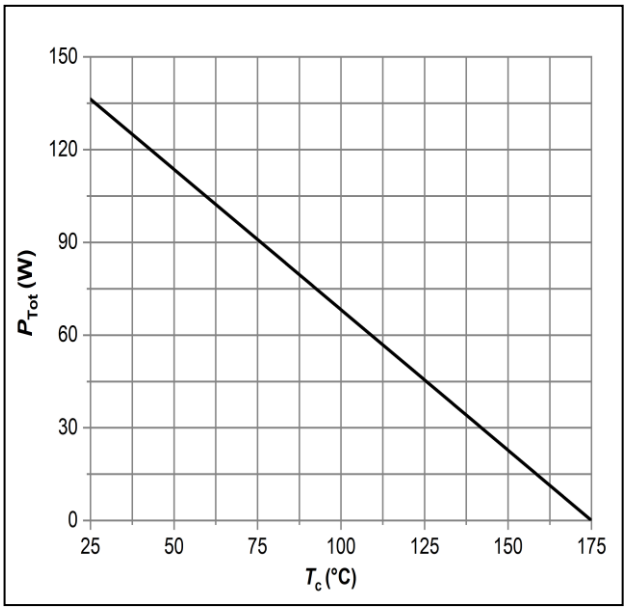


Figure 4: Power Derating

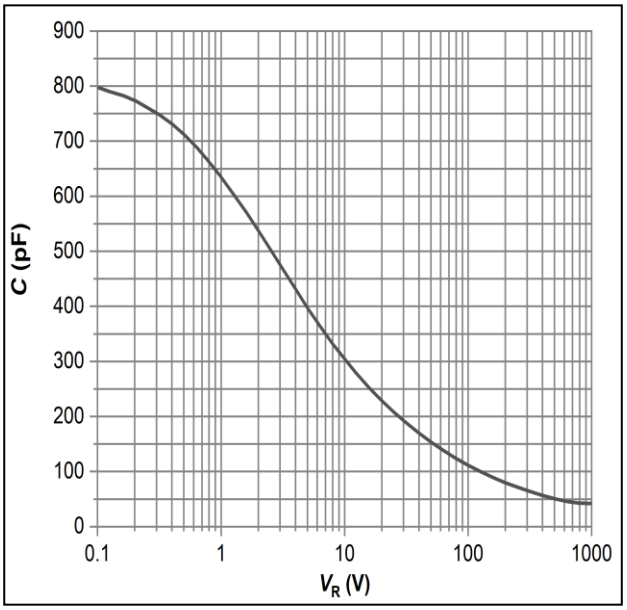


Figure 5: Capacitance vs. Reverse Voltage

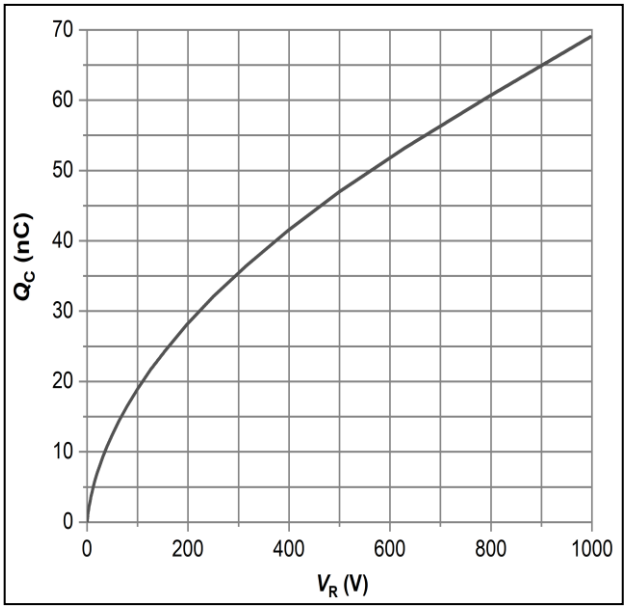


Figure 6: Total Capacitance Charge vs. Reverse Voltage

Typical Performance

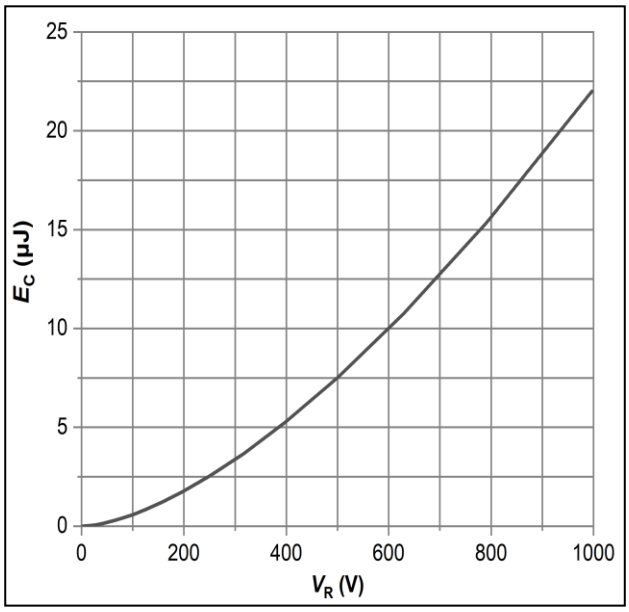


Figure 7:Typical Capacitance Stored Energy

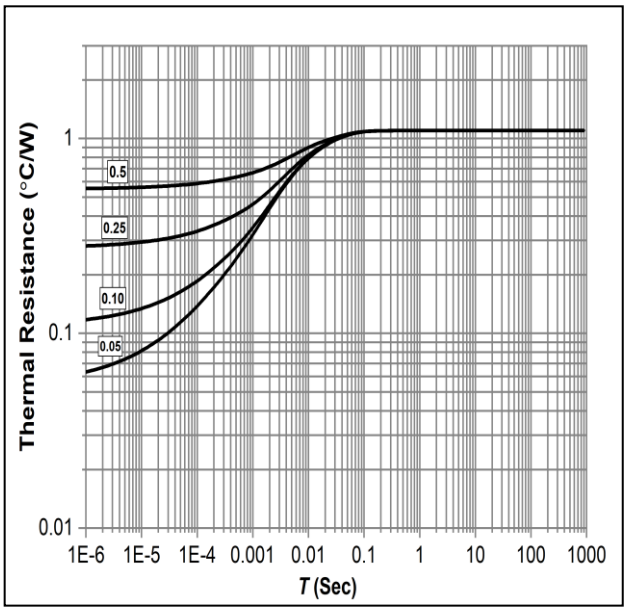


Figure 8: Transient Thermal Impedance

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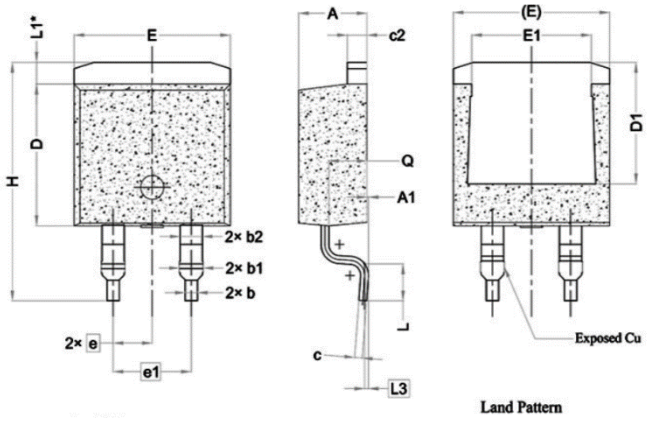
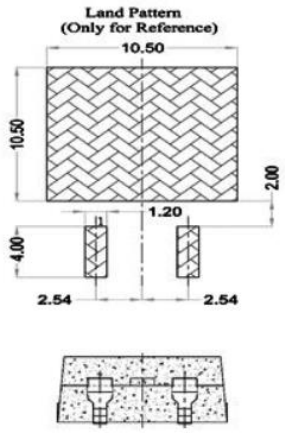
Package Dimensions

Package：TO-263-2





单位：mm

SYMBOL	DIMENSIONS		
	MIN.	NOM.	MAX.
A	4.24	4.44	4.64
A1	0.00	0.10	0.25
b	0.70	0.80	0.90
b1	1.20	1.55	1.75
b2	1.20	1.45	1.70
c	0.40	0.50	0.60
c2	1.15	1.27	1.40
D	8.82	8.92	9.02
D1	6.86	7.65	---
E	9.96	10.16	10.36
E1	6.89	7.77	7.89
e	2.54 BSC		
e1	5.08 BSC		
H	14.61	15.00	15.88
L	1.78	2.32	2.79
L1	1.36 REF.		
L3	0.25 BSC		
Q	2.30	2.48	2.70